

ABSTRACT

To provide a semiconductor light emitting device capable of improving an aspect ratio of a laser beam to make it close to a circular shape and a method of producing the same, a first conductive type first cladding layer 11, an active layer 12, and a second conductive type second cladding layer 17 having a ridge-shaped portion RD as a current narrowing structure are stacked on a substrate 10; wherein the ridge-shaped portion includes a first ridge-shaped layer 15 on the side close to said active layer and having a high bandgap and a second ridge-shaped layer 16 on the side distant from the active layer and having a low bandgap, so that the semiconductor light emitting device is obtained. By using an epitaxial growth method, a first cladding layer, active layer and second conductive type second cladding layer are formed by being stacked on the substrate, a part of the second cladding layer is processed to be a ridge-shaped portion, and the second cladding layer is formed, so that the portion to be a ridge shape includes the first ridge-shaped layer and second ridge-shaped layer.